PATENT ABSTRACTS OF JAPAN

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(54) STORAGE

(57) Abstract:

PROBLEM TO BE SOLVED: To improve the access speed by deciding whether the data should be interleaved according to the quantity of data to be written at a time and then writing the data in a flash memory.

SOLUTION: When the logical address of a storage and the information to be written are given from an external I/F, a controller 101 decides a specific area of a flash memory 102 where the data are actually written on an address conversion table existing at a part of the memory 102. The conversion table that is defined every 16 sectors (8448 bytes), for example, contains a bit to show whether the data should be interleaved. The controller 101 decides the said interleaving according to the quantity of data to be written at a time, sets a bit showing the interleaving in the conversion table if the interleaving is advantageous and writes the 1st and 2nd data in the flash memories 102 and 103 respectively. Thereafter, the data are alternately and continuously

written in both memories 102 and 103 and accordingly the writing time is shortened.

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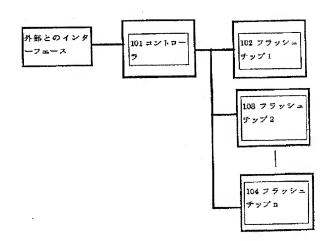
Fターム(参考) 5B060 HA02

(54) 【発明の名称】 記憶装置

(57)【要約】

【課題】フラッシュメモリを使用した記憶装置のアクセ ス時間を短くすることにある。

【解決手段】フラッシュメモリを使用した記憶装置にデ ータを書き込む場合一度に書き込むデータ量に応じてイ ンターリーブするかしないかを決定し書き込みを行う。



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【特許請求の範囲】

【請求項1】複数のフラッシュメモリチップとその制御を行うコントローラにより構成される記憶装置において概記憶装置に書込むデータをフラッシュメモリの連続したアドレスに書込むかあるいは複数のフラッシュメモリに交互に書込むかを決めるビットがありそのビットにしたがって書込み方法を切り替えることを特徴とする記憶装置。

【発明の詳細な説明】

[0001]

【発明の属する技術分野】本発明はフラッシュメモリを 使用した記憶装置に関するものである。

[0002]

【従来の技術】複数のフラッシュメモリとその制御を行 うコントローラにより構成される記憶装置ではそのデー タの書き込みおよび読み出しをする場合にコントローラ のシンリンダー、トラック、セクタにより構成される論 理アドレスを変換テーブルによりコントローラがフラッ シュメモリの物理アドレスに対応させていた。このコン トローラがインターリーブという方法によりフラッシュ メモリへの書き込み時間を短くしていた。インターリー ブとは連続したデータを1つのフラッシュメモリの連続 したアドレスに書き込むのではなく複数のメモリにまた がって書き込む方法である。たとえば10セクタのデータ を書込む場合には、1セクタは512バイトとそのデータ の管理情報16バイトの合計528バイトで構成されるので5 28×10バイトのデータをフラッシュメモリに書込む必要 がある。フラッシュメモリに書込みを行う場合528バイ トのデータをフラッシュメモリチップに転送しフラッシ ュメモリ内部のバッファに格納した後、フラッシュメモ 30 リに書込みコマンドを発行しフラッシュメモリにデータ を書込む。フラッシュメモリチップにデータを転送する のに要する時間をtT、フラッシュメモリにデータを書込 む時間をtWとすると10セクタ分のデータを1つのフラッ シュメモリチップに書込むのに要する時間は10×(t T+tW) である。

【0003】インターリーブでは10ある528バイト単位のデータのうち最初の528バイトデータをk番目のフラッシュメモリチップに書込み、次の528バイトデータをk+1番目のフラッシュメモリチップに書込み3番目の528バイトデータを再度k番目のフラッシュメモリに書込むという動作をする。

【0004】このようにするとk番目のフラッシュメモリに528バイトデータの書込みが完了するまでの時間を待たずにk+1番目のフラッシュメモリチップにデータの転送を開始できる。したがって10セクタ分のデータを書込むのに要する時間は5×(tT+tW)+tTである。一般にtT<tWであるためインターリーブ動作をするとインターリーブをしない場合に比べて書込み時間が約半分になる。

[0005]

【発明が解決しようとする課題】しかしながら全ての書 き込み動作に対してインターリーブを行うとかえって記 憶装置としてアクセス時間を長くさせるという問題があ った。たとえば記憶装置の中の1セクタのみのデータを 書き換える動作を行う場合には528バイトのみのデータ を書き換えれば良いはずである。しかしフラッシュメモ リはたとえば528×16=8448バイトで構成されるブロック の単位で書き込みを行う。これは以下の理由による。フ ラッシュメモリは現在書込んであるデータに上書きをす ることができず8448バイトの単位で一旦データを消去し て書込みを行う。ある8448バイトのブロック内部の528 バイトを書換える場合には8448のうち528バイトのみの イレーズすることはできないので従来格納されていた84 48バイトのデータのうち528バイトのみ変更した8448バ イトのデータを同じアドレス領域をイレーズした後再度 書込むかあるいは他のイレーズ済みのエリアに書込む。 いずれにしても8448バイト(528バイトを16回)の書込 みが必要である。よってひとつのブロックの書込みを行 う場合には16×(tT+tW)の時間を要する。これは1セ クタのみ書換える場合でも複数セクタのデータを書換え る場合でも同じ時間が必要である。

【0006】たとえば2セクタのみの書込みが必要な場合にはインターリーブを行うと16×(tT+tW)+tTの時間が必要であるがインターリーブを行わなければ16×(tT+tW)で書込みが終了する。一方16を超えるセクタの書込みを行う場合にはインターリーブした方が早くなる。17セクタの書込みを行う場合には2つの8448バイトのブロックの書込みを行う必要がある。インターリーブを行わないと一つ目のフラッシュメモリの16セクタのデータを書換えた後2つ目のフラッシュメモリの16セクタデータを書換える必要があるので2×16×(tT+tW)-tWの時間が必要である。しかしインターリーブを行うと16×(tT+tW)+tTで書込みができる。

【0007】以上のようにインターリーブを行うことにより書込み時間が早くなる場合と遅くなる場合がある。 【0008】

【課題を解決するための手段】本発明の記憶装置は、複数のフラッシュメモリチップとその制御を行うコントローラにより構成される記憶装置において概記憶装置に書込むデータをフラッシュメモリの連続したアドレスに書込むかあるいは複数のフラッシュメモリに交互に書込むかを決めるビットがありそのビットにしたがって書込み方法を切り替えることを特徴とする。

[0009]

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【発明の実施の形態】図1が本発明のブッロク図である。101はコントローラでありコントローラ101にはコントローラの処理を行うCPUとコントローラの処理プログラムを行うROMとCPUが一時的に必要なデータを保存する50 RAMとフラッシュメモリのデータの読み書きを行うため

のアドレス、データバスおよび記憶装置の外部とやりと りをするインターフェースから構成される。102,103は フラッシュメモリでありコントローラ101によりアクセ スされる。本実施例ではフラッシュメモリが2個の場合 を説明しているがフラッシュメモリは2個以上ならいく つでも構わない。

【0010】外部インタフェースからシリンダ、トラッ ク、セクタという記憶装置の論理アドレスと書込む情報 がコントローラ101に与えられるとコントローラ101はフ ラッシュメモリ102の一部にあるアドレス変換テーブル により実際のフラッシュメモリのどのエリアにデータを 書込むかを決定する。

【0011】このアドレス変換テーブルを図2に示す。 シリンダ、トラック、セクタがこのアドレス変換テーブ ルに入力されるとそれに対応したフラッシュメモリのア ドレスが出力される。このアドレスにデータを書き込 む。変換テーブルは16セクタ(8448バイト)毎に定義さ れている。このアドレス変換テーブルにはインターリー ブするかどうかを示すビットがある。一度に書き込むデ ータ量によりインターリーブしたほうが有利かどうかを 20 コントローラ101が判断し、有利なら変換テーブル内の インターリーブを示すビットをセットし、フラッシュメ モリ102,103にまたがりデータを書き込む。

【0012】データを書き込む方法を図3に示す。フラ ッシュメモリは8448単位のブロックがいくつか含まれる がフラッシュメモリ102,103の同時位置にあるブロック を使って図3のようにデータを書き込む。図3の数字が データを書き込む順番を示す。1番目のデータをフラッ シュメモリ102に書き込み、2番目のデータをフラッシ *

*ュメモリ103に書き込む。以下同様に奇数番のデータを フラッシュメモリ102に偶数番のデータをフラッシュメ モリ103に書き込む。このデータを読み出す場合にはア ドレス変換テーブルのインターリーブを示すビットを読 みフラッシュメモリ102と103から交互にデータを読み出 す。もし一度に書き込むデータ量が少ない場合にはアド レス変換テーブルのインターリーブを示すビットをリセ ットし図4に示すように一つのフラッシュメモリに連続 してデータを書き込む。このデータを読み出す場合には 10 アドレス変換テーブルのインターリーブを示すビットを 参照し連続したデータを読み出す。

[0013]

【発明の効果】以上のように1度に書き込むデータ量に よりインターリーブをするかしないかを判断してフラッ シュメモリに書き込むことによりアクセス速度を早くす ることができる。

【図面の簡単な説明】

本発明の1実施の形態を示すシステム構成 【図1】 义。

【図2】 アドレス変換テーブルの図。

インターリーブした場合のデータ書き込み 【図3】 例の図。

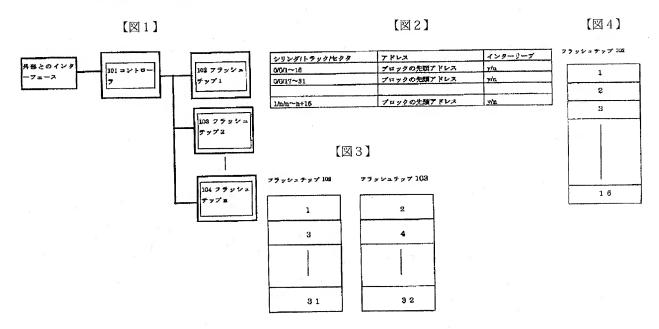
インターリーブしない場合のデータ書き込 【図4】 み例の図。

【符号の説明】

101 コントローラ

102 フラッシュメモリ

103 フラッシュメモリ



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CLAIMS

[Claim(s)]

[Claim 1]By two or more flash memory chips and a controller which performs the control. Memory storage changing a method which there is a bit to decide and writes in whether data written in ******** in memory storage constituted is written in an address with which a flash memory continued, or it writes in two or more flash memories by turns according to the bit.

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DETAILED DESCRIPTION

[Detailed Description of the Invention] [0001]

[Field of the Invention] This invention relates to the memory storage which uses a flash memory. [0002]

[Description of the Prior Art]When making writing and read-out of the data two or more flash memories with the memory storage constituted by the controller which performs the control, SHINRINDA of a controller, The controller was making the track and the logical address constituted by the sector correspond to the physical address of a flash memory with a translation table. This controller shortened writing time to the flash memory by the method of interleave. Interleave is a method which does not write continuous data in the address with which one flash memory continued, but is written in ranging over two or more memories. For example, to write in the data of ten sectors, since one sector comprises 512 bytes and a total of 528 bytes of 16 bytes of management information of the data, it needs to write 528x10 bytes of data in a flash memory. When writing in a flash memory, after transmitting 528 bytes of data to a flash memory

chip and storing in the buffer inside a flash memory, a write command is published to a flash memory and data is written in a flash memory. When time to write data for the time taken to transmit data to a flash memory chip in tT and a flash memory is set to tW, the time taken to write the data for ten sectors in one flash memory chip is 10x (tT+tW).

[0003]The first 528 byte data are written in the k-th flash memory chip among the data of the 528-byte unit which exists ten in interleave, Operation of writing the 528 following byte data in the k+1st flash memory chips, and writing the 3rd 528 byte data in the k-th flash memory again is carried out.

[0004]If it does in this way, a data transfer can be started to the k+1st flash memory chips, without waiting for time until the writing of 528 byte data is completed to the k-th flash memory. Therefore, the time taken to write in the data for ten sectors is 5x(tT+tW)+tT. Compared with the case where it will not interleave if interleave operation is carried out, since it is generally tT < tW, a write time becomes abbreviation half.

[0005]

[Problem to be solved by the invention]However, when interleaved to all the writing operation, there was a problem of lengthening access time as memory storage on the contrary. For example, what is necessary must be just to rewrite 528 bytes of data, when performing operation which rewrites the data of only one sector in memory storage. However, a flash memory writes in in the unit of the block which comprises $528 \times 16 = 8448$ byte. This is based on the following Reasons. A flash memory cannot be overwritten at the data written in now, but writes in by once eliminating data in the unit which is 8448 bytes. In rewriting 528 bytes inside 8448 bytes of a certain block, among 8448 by 528 bytes of that which can be erased and is twisted. After erasing the same address area, 8448 bytes of data which was accepted 528 bytes of 8448 bytes of data stored conventionally, and was changed is written in again, or is written in the area erased [other]. Anyway, 8448 bytes (it is 16 times about 528 bytes) of writing is required. Therefore, in writing in one block, it requires the time of 16x (tT+tW). When rewriting only one sector, or when rewriting the data of two or more sectors, the same time is required for this.

[0006]For example, if the time of 16x(tT+tW)+tT is required if it interleaves when the writing of only two sectors is required, but it does not interleave, writing is completed by 16x(tT+tW). In writing in the sector exceeding 16 on the other hand, the interleaved direction becomes early. To write in 17 sectors, it is necessary to write in 8448 bytes of two blocks. Since it is necessary to rewrite 16 sector data of the 2nd flash memory after rewriting the data of 16 sectors of a one-eyed flash memory if it does not interleave, the time of 2x16x(tT+tW)-tW is required. However, if it interleaves, writing will be made in 16x(tT+tW)+tT.

[0007]It may become late with the case where a write time becomes early, by interleaving as mentioned above.

[8000]

[Means for solving problem] The memory storage of this invention, By two or more flash memory chips and the controller which performs the control. The method which there is a bit to decide and writes in whether the data written in ******** in the memory storage constituted is written in the address with which the flash memory continued, or it writes in two or more flash memories by turns according to the bit is changed.

[0009]

[Mode for carrying out the invention] <u>Drawing 1</u> is a BURROKU figure of this invention. The address for 101 being a controller and writing the data of CPU which processes a controller, RAM where ROM and CPU which perform the processing program of a controller save data

required for a target temporarily, and a flash memory for the controller 101, It comprises an interface exchanged with the exterior of a data bus and memory storage. 102,103 is a flash memory and is accessed by the controller 101. In this example, although the case where the number of flash memories is two is explained, two or more flash memories may be learned and shoes may be sufficient as them.

[0010]The cylinder from an external interface, a track, It is determined in which area of a actual flash memory data is written with the address mapping table which the controller 101 has in a part of flash memory 102 as the logical address of memory storage called a sector and the information to write in are given to the controller 101.

[0011]This address mapping table is shown in <u>drawing 2</u>. If a cylinder, a track, and a sector are inputted into this address mapping table, the address of the flash memory corresponding to it will be outputted. Data is written in this address. The translation table is defined as every 16 sectors (8448 bytes). The bit which shows whether it interleaves or not is shown in this address mapping table. The controller 101 judges that it is more advantageous whether to interleave with the data volume written in at once, if advantageous, the bit which shows the interleave in a translation table is set, and data is written in ranging over the flash memory 102,103.

[0012]How to write in data is shown in <u>drawing 3</u>. A flash memory writes in data like <u>drawing 3</u> using the block in the simultaneous position of the flash memory 102,103, although some blocks of 8448 units are included. The turn that the number of <u>drawing 3</u> writes in data is shown. The 1st data is written in the flash memory 102, and the 2nd data is written in the flash memory 103. Like the following, the data of No. odd is written in the flash memory 102, and the data of No. even is written in the flash memory 103. In reading this data, the bit which shows interleave of an address mapping table is read, and it reads data from the flash memories 102 and 103 by turns. When there is little data volume written in at once, as the bit which shows interleave of an address mapping table is reset and it is shown in <u>drawing 4</u>, data is written in succeeding one flash memory. In reading this data, it reads the data which continued with reference to the bit which shows interleave of an address mapping table.

[Effect of the Invention] An access speed can be early carried out by interleaving with the data volume written in at a time as mentioned above judging whether lends and there is, and writing in a flash memory.

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TECHNICAL FIELD

[Field of the Invention] This invention relates to the memory storage which uses a flash memory.

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PRIOR ART

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EFFECT OF THE INVENTION

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TECHNICAL PROBLEM

[Problem to be solved by the invention] However, when interleaved to all the writing operation, there was a problem of lengthening access time as memory storage on the contrary. For example, what is necessary must be just to rewrite 528 bytes of data, when performing operation which rewrites the data of only one sector in memory storage. However, a flash memory writes in in the unit of the block which comprises 528x16=8448 byte. This is based on the following Reasons. A flash memory cannot be overwritten at the data written in now, but writes in by once eliminating data in the unit which is 8448 bytes. In rewriting 528 bytes inside 8448 bytes of a certain block, among 8448 by 528 bytes of that which can be erased and is twisted. After erasing the same address area, 8448 bytes of data which was accepted 528 bytes of 8448 bytes of data stored conventionally, and was changed is written in again, or is written in the area erased [other]. Anyway, 8448 bytes (it is 16 times about 528 bytes) of writing is required. Therefore, in writing in one block, it requires the time of 16x (tT+tW). When rewriting only one sector, or when rewriting the data of two or more sectors, the same time is required for this. [0006]For example, if the time of 16x(tT+tW)+tT is required if it interleaves when the writing of only two sectors is required, but it does not interleave, writing is completed by 16x (tT+tW). In writing in the sector exceeding 16 on the other hand, the interleaved direction becomes early. To write in 17 sectors, it is necessary to write in 8448 bytes of two blocks. Since it is necessary to rewrite 16 sector data of the 2nd flash memory after rewriting the data of 16 sectors of a oneeyed flash memory if it does not interleave, the time of 2x16x(tT+tW)-tW is required. However,

if it interleaves, writing will be made in 16x(tT+tW)+tT.

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MEANS

[Means for solving problem] The memory storage of this invention, By two or more flash memory chips and the controller which performs the control. The method which there is a bit to decide and writes in whether the data written in ******** in the memory storage constituted is written in the address with which the flash memory continued, or it writes in two or more flash memories by turns according to the bit is changed.

[0009]

[Mode for carrying out the invention] <u>Drawing 1</u> is a BURROKU figure of this invention. The address for 101 being a controller and writing the data of CPU which processes a controller, RAM where ROM and CPU which perform the processing program of a controller save data required for a target temporarily, and a flash memory for the controller 101, It comprises an interface exchanged with the exterior of a data bus and memory storage. 102,103 is a flash memory and is accessed by the controller 101. In this example, although the case where the number of flash memories is two is explained, two or more flash memories may be learned and shoes may be sufficient as them.

[0010]The cylinder from an external interface, a track, It is determined in which area of a actual flash memory data is written with the address mapping table which the controller 101 has in a part of flash memory 102 as the logical address of memory storage called a sector and the information to write in are given to the controller 101.

[0011]This address mapping table is shown in <u>drawing 2</u>. If a cylinder, a track, and a sector are inputted into this address mapping table, the address of the flash memory corresponding to it will be outputted. Data is written in this address. The translation table is defined as every 16 sectors (8448 bytes). The bit which shows whether it interleaves or not is shown in this address mapping table. The controller 101 judges that it is more advantageous whether to interleave with the data volume written in at once, if advantageous, the bit which shows the interleave in a translation table is set, and data is written in ranging over the flash memory 102,103.

[0012]How to write in data is shown in <u>drawing 3</u>. A flash memory writes in data like <u>drawing 3</u> using the block in the simultaneous position of the flash memory 102,103, although some blocks of 8448 units are included. The turn that the number of drawing 3 writes in data is shown. The

1st data is written in the flash memory 102, and the 2nd data is written in the flash memory 103. Like the following, the data of No. odd is written in the flash memory 102, and the data of No. even is written in the flash memory 103. In reading this data, the bit which shows interleave of an address mapping table is read, and it reads data from the flash memories 102 and 103 by turns. When there is little data volume written in at once, as the bit which shows interleave of an address mapping table is reset and it is shown in drawing 4, data is written in succeeding one flash memory. In reading this data, it reads the data which continued with reference to the bit which shows interleave of an address mapping table.

[Translation done.] * NOTICES *

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DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] The system configuration figure showing 1 embodiment of this invention.

[Drawing 2] The figure of an address mapping table.

Drawing 3] The figure of the example of data writing at the time of interleaving.

[Drawing 4] The figure of the example of data writing when not interleaving.

[Explanations of letters or numerals]

101 Controller

102 Flash memory

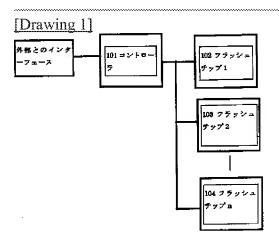
103 Flash memory

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DRAWINGS

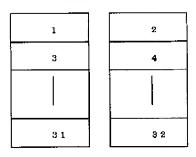


[Drawing 2]

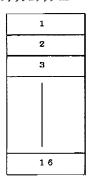
シリンダルラック性クタ	アドレス	インターリーブ
0/0/1~16	ブロックの先頭アドレス	y/n.
0/0/17~31	ブロックの先頭アドレス	9/2,
1/n/n~n+15	プロックの先頭アドレス	yht

[Drawing 3]

フラッシュチップ 103



[Drawing 4]



[Translation done.]